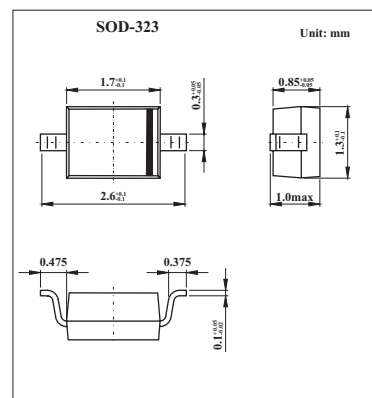


Silicon Epitaxial Planar Diode

1SV328

■ Features

- High Capacitance Ratio: $C_{1V}/C_{4V}=2.8$ (Typ.)
- Low Series Resistance: $r_s=0.55\ \Omega$ (Typ.)
- Useful for Small Size Tuner

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1\ \mu\text{A}$	10			V
Reverse Current	I_R	$V_R = 10\text{ V}$			3	nA
Capacitance	C_{1V}	$f = 1\text{ MHz}; V_R = 1\text{ V}$	5.7		6.7	pF
	C_{4V}	$f = 1\text{ MHz}; V_R = 4\text{ V}$	1.85		2.45	
Capacitance Ratio	C_{1V}/C_{4V}		2.7	2.8		
Series Resistance	r_s	$V_R = 1\text{ V}, f = 470\text{ MHz}$		0.55	0.7	Ω

Note

1.Signal level when capacitance is measured: $V_{sig} = 100\text{mV}_{rms}$

■ Marking

Marking	V2
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